

SEP 26 2006

SHEET 1 OF 1

Form PTO 1449  
(Modified)DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY DOCKET NO.  
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10/580,833

## LIST OF REFERENCES CITED BY APPLICANT

APPLICANT  
Kazuhito YASUDA, et al.FILING DATE  
May 26, 2006

GROUP

## U.S. PATENT DOCUMENTS

| EXAMINER INITIAL | DOCUMENT NUMBER | DATE | NAME | CLASS | SUB CLASS | FILING DATE IF APPROPRIATE |
|------------------|-----------------|------|------|-------|-----------|----------------------------|
| AA               |                 |      |      |       |           |                            |
| AB               |                 |      |      |       |           |                            |
| AC               |                 |      |      |       |           |                            |
| AD               |                 |      |      |       |           |                            |
| AE               |                 |      |      |       |           |                            |
| AF               |                 |      |      |       |           |                            |
| AG               |                 |      |      |       |           |                            |
| AH               |                 |      |      |       |           |                            |
| AI               |                 |      |      |       |           |                            |
| AJ               |                 |      |      |       |           |                            |
| AK               |                 |      |      |       |           |                            |
| AL               |                 |      |      |       |           |                            |
| AM               |                 |      |      |       |           |                            |
| AN               |                 |      |      |       |           |                            |

## FOREIGN PATENT DOCUMENTS

|    | DOCUMENT NUMBER | DATE | COUNTRY | TRANSLATION<br>YES | NO |
|----|-----------------|------|---------|--------------------|----|
| AO |                 |      |         |                    |    |
| AP |                 |      |         |                    |    |
| AQ |                 |      |         |                    |    |
| AR |                 |      |         |                    |    |
| AS |                 |      |         |                    |    |

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

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| /MG/ | AY | LEO, G. et al., "Influence of a ZnTe Buffer Layer on the Structural Quality of CdTe Epilayers Grown on (100) GaAs by Metalorganic Vapor Phase Epitaxy", J.Vac.Technol.B., Vol. 14, No. 3, pgs 1739-1744, 1996.                                 |  |
|      | AZ |  | <input type="checkbox"/> Additional References sheet(s) attached |

Examiner /Mark Gaworecki/

Date Considered 07/14/2007

\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.